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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Stephanie Daryae
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Applicant : Jan S. Iwanczyk, et al.
Application No. : 09/835,937
Filed : April 16, 2001
Title : JUNCTION-SIDE ILLUMINATED
SILICON DETECTOR ARRAYS

Grp./Div. : 2878
Examiner : Constantine Hannaher

Docket No. : 41876/RAG/P590

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Post Office Box 7068
Pasadena, CA 91109-7068
April 18, 2003

Commissioner:

In response to the Office action of December 18, 2002, please amend the above-identified application as follows:

In the Specification:

On page 2, lines 8-19, please replace with the following paragraphs:

Other broad applications including radiation hardened detector arrays for high-energy physics research would also benefit from a development of low cost, high-yield detector array structures.

Typical silicon photodiode arrays with parallel signal readout are based on (p+) - (n) - (n+) structures constructed on high resistivity (1 - 100 ohm-m) silicon wafers. P+ contacts forming junctions in the n-type substrate are constructed in the form of a diode array. A